



Docket No.: MUH-11086

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By: h.p. ~

Date: September 5, 2001

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants : Wolfgang Werner
Applic. No. : 09/931,689
Filed : August 16, 2001
Title : IGBT With PH Insulation and Production Method

INFORMATION DISCLOSURE STATEMENT

Hon. Commissioner of Patents and Trademarks,
Washington, D.C. 20231

Sir:

In accordance with 37 C.F.R. 1.98 copies of the following patents and/or publications are submitted herewith:

DP U. S. Patent 5,801,420 (Fujishima) dated September 1, 1998;

European Patent Application 0 338 312 A2 (Sakurai et al.) dated October 25, 1989;

European Patent Application 0 273 030 A2 (Baliga) dated June 29, 1988;

European Patent Application 0 420 672 A1 (Ogura et al.) dated April 3, 1991;

European Patent Application 0 767 499 A2 (Yamazaki) dated April 9, 1997;

European Patent Application 0 915 508 A1 (Pozzoni) dated May 12, 1999;

07 East German Patent 148 546 (Armgarth) dated May 27, 1981, pertains to a double epitaxial process for the production of unipolar and bipolar semiconductor structures;

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PF German Published, Non-Prosecuted Patent Application DE 198 05 786 (Werner)
dated August 26, 1999, pertains to a semiconductor component structured to avoid
leakage current;

DF German Published, Non-Prosecuted Patent Application DE 37 25 429 A1 (Kalkhof)
dated February 9, 1989;

b.F. German Published, Non-Prosecuted Patent Application 1 564 547 (Goshgarian)
dated May 21, 1970, pertains to a semiconductor-micro circuit element;

DF Patent Abstract of Japan 03245562 (Tanaka Masaharu) dated November 1, 1991;

DF Patent Abstract of Japan 63081861 (Mitarai Goro) dated April 12, 1988;

DF Disney et al.: "SOI LIGBT Devices with a Dual P-Well Implant for Improved Latching
Characteristics" 5th International Symposium on Power Semiconductor Devices and
ICs, 1993 IEEE, pages 254 - 258;

DF Udrea et al.: "Lateral Insulated Gate Bipolar Transistor (LIGBT) Structure Based on
Partial Isolation SOI Technology" Electronics Letters, May 8, 1997, Vol. 33, No. 10,
pages 907 - 909;

DF Simpson et al.: "Analysis of the Lateral Insulated Gate Transistor", IEDM 85, 1985
IEEE, pages 740 - 743.

Don Shi

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